PAN82TE36S

Dual N-Ch 20V Fast Switching MOSFET

V_{DS}=20V, I_D=6.0A, $R_{DS(ON)}$=22mΩ

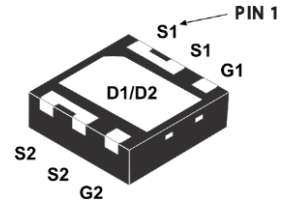
➢ General Description

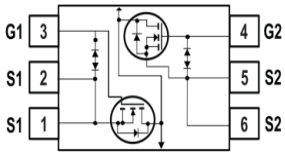
This PAN82TE36S Dual N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➢ Feature

- ●Super Low Gate Charge
- ●Green Device Available
- ●Excellent CdV/dt effect decline
- ●ESD Protected
- ●Advanced high cell density Trench technology
- ●DFN2X2A-EP3 package design

➢ DFN2X2A-EP3





➢ Application

- ●Load Switch
- ●Portable Equipment
- ●Battery Powered System

➢ Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current[1]	I_D@T_A=25℃	6	A
Continuous Drain Current[1]	I_D@T_A=70℃	4.8	A
Pulsed Drain Current[2]	I_{DM}	36	A
Total Power Dissipation[3]	P_D@T_A=25℃	1.4	W
Storage Temperature Range	T_{STG}	-55 to 150	℃
Operating Junction Temperature Range	T_J	-55 to 150	℃
Thermal Resistance Junction-ambient [1]	$R_{\theta JA}$	90	℃/W

➢ Electrical Characteristics (T_J=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V , I_D=250uA	20	---	---	V
Static Drain-Source On-Resistance[2]	$R_{DS(ON)}$	V_{GS}=4.5V , I_D=3.0A	14.0	17.5	22.0	mΩ
		V_{GS}=4.0V , I_D=3.0A	14.5	18.0	22.5	
		V_{GS}=3.7V , I_D=3.0A	15.0	18.5	23.0	
		V_{GS}=3.1V , I_D=3.0A	15.5	19.5	25.0	
		V_{GS}=2.5V , I_D=3.0A	17.5	22.0	29	
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS} , I_D =250uA	0.5	0.7	1.5	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=16V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=16V , V_{GS}=0V , T_J=55℃	---	---	5	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±8V , V_{DS}=0V	---	---	±10	uA
Forward Transconductance	gfs	V_{DS}=5V , I_D=3.0A	---	20	---	S
Total Gate Charge	Q_g	V_{DS}=15V , V_{GS}=4.5V , I_D=6A	---	10.4	---	nC
Gate-Source Charge	Q_{gs}		---	1.3	---	
Gate-Drain Charge	Q_{gd}		---	2.6	---	
Turn-On Delay Time	$T_{d(on)}$	V_{DD}=10V , V_{GS}=4.5V , R_G=3.3Ω I_D=3A	---	3.2	---	ns
Rise Time	T_r		---	9.8	---	
Turn-Off Delay Time	$T_{d(off)}$		---	31	---	
Fall Time	T_f		---	3.6	---	
Input Capacitance	C_{iss}	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	630	---	pF
Output Capacitance	C_{oss}		---	66	---	
Reverse Transfer Capacitance	C_{rss}		---	63	---	

➢ Diode Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current[1,4]	I_S	V_G=V_D=0V , Force Current	---	---	6	A
Diode Forward Voltage[2]	V_{SD}	V_{GS}=0V , I_S=1A , T_J=25℃	---	0.86	1.2	V

Note :
1.Pulse width limited by maximum junction temperature.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.Ensure that the channel temperature does not exceed 150°C.
4.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

➢ Typical Characteristics

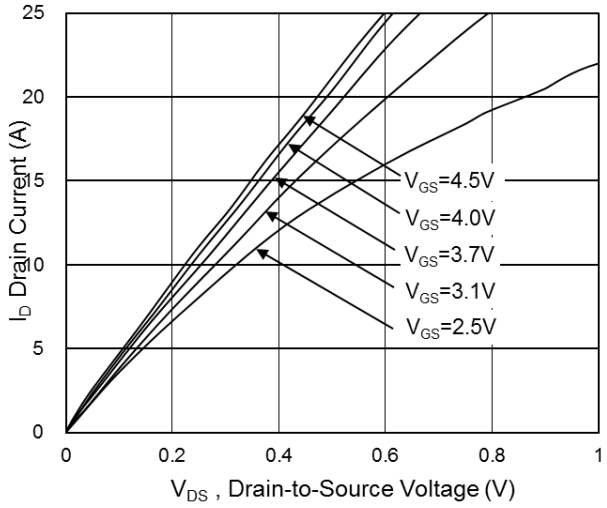


Fig.1 Typical Output Characteristics

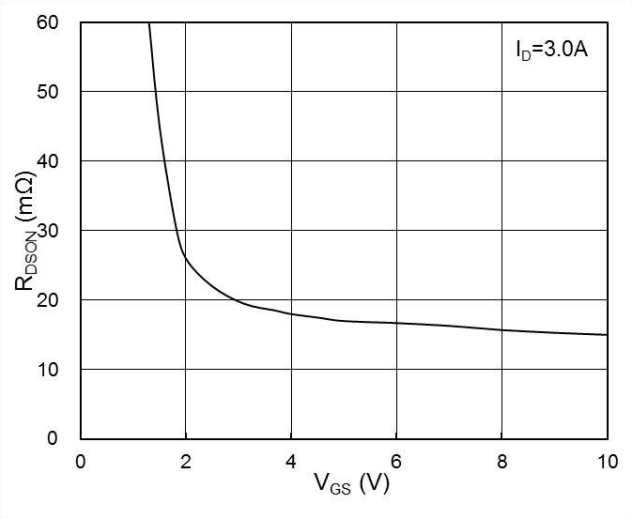


Fig.2 On-Resistance vs. Gate-Source voltage

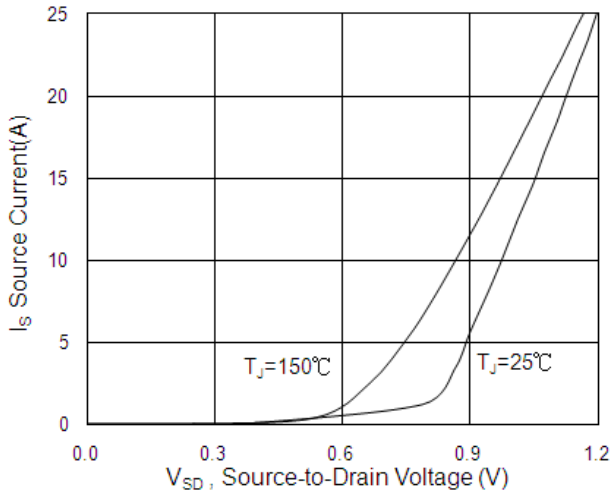


Fig.3 Forward Characteristics Of Reverse

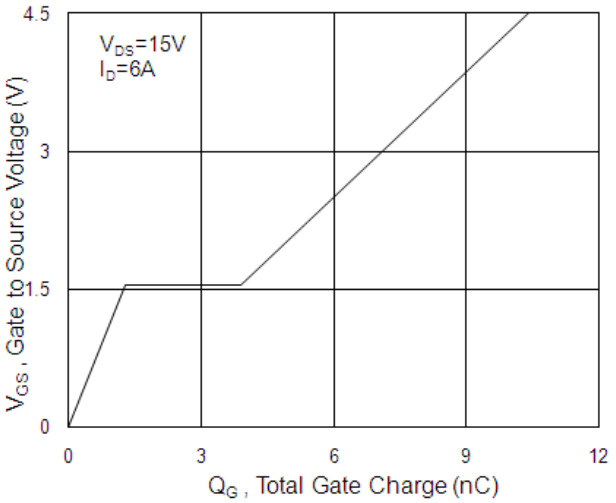


Fig.4 Gate-Charge Characteristics

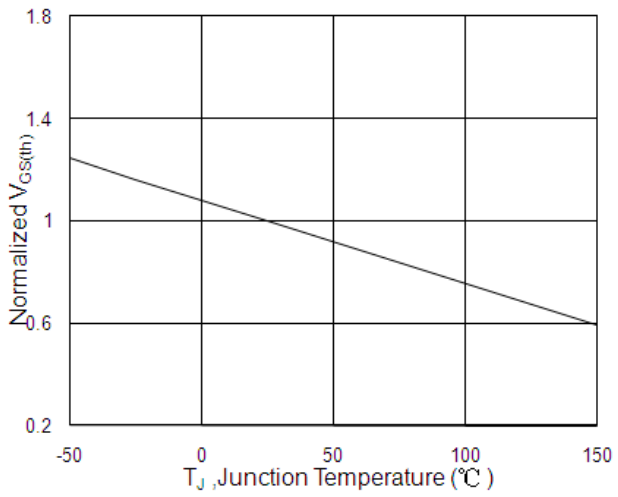


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

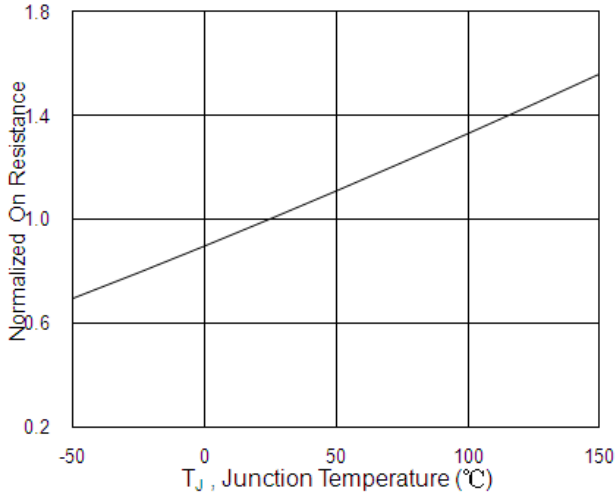


Fig.6 Normalized R_{DSON} vs. T_J

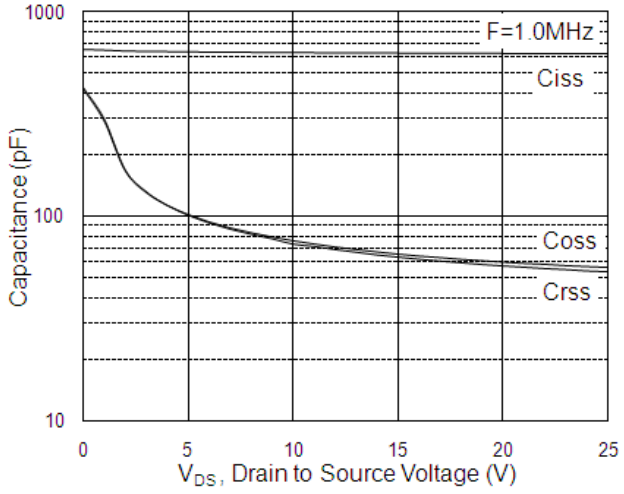


Fig.7 Capacitance

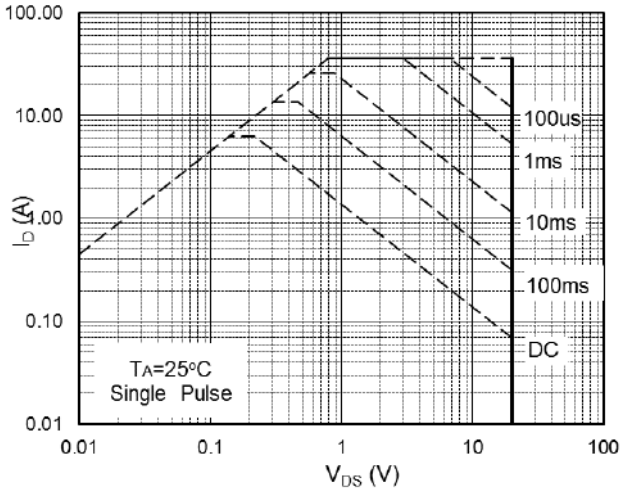


Fig.8 Safe Operating Area

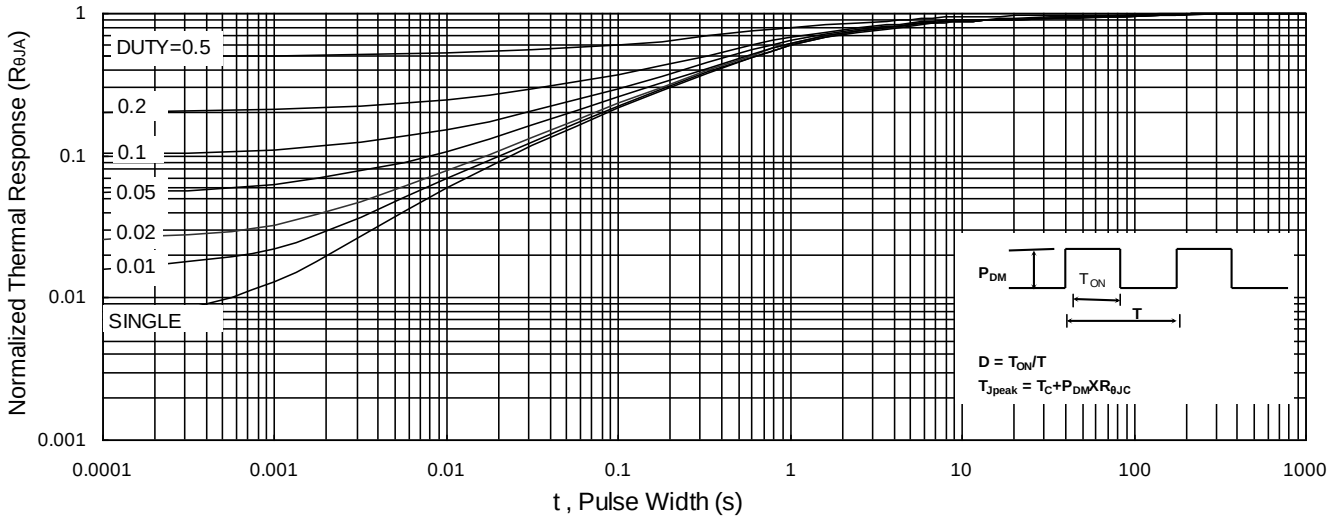


Fig.9 Normalized Maximum Transient Thermal Impedance

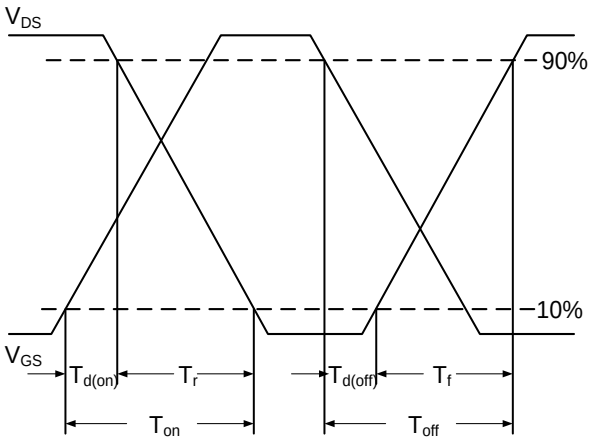


Fig.10 Switching Time Waveform

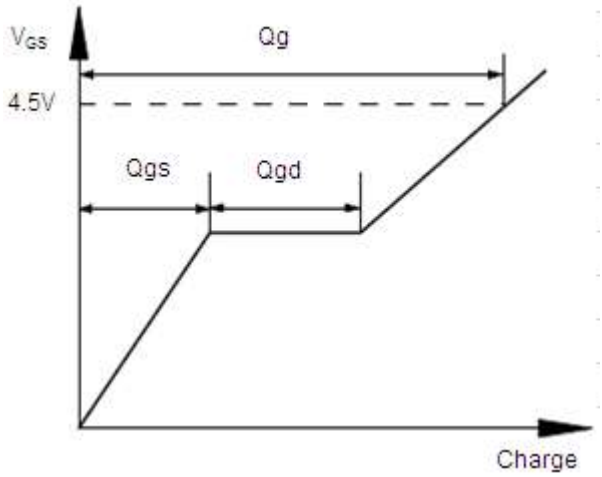
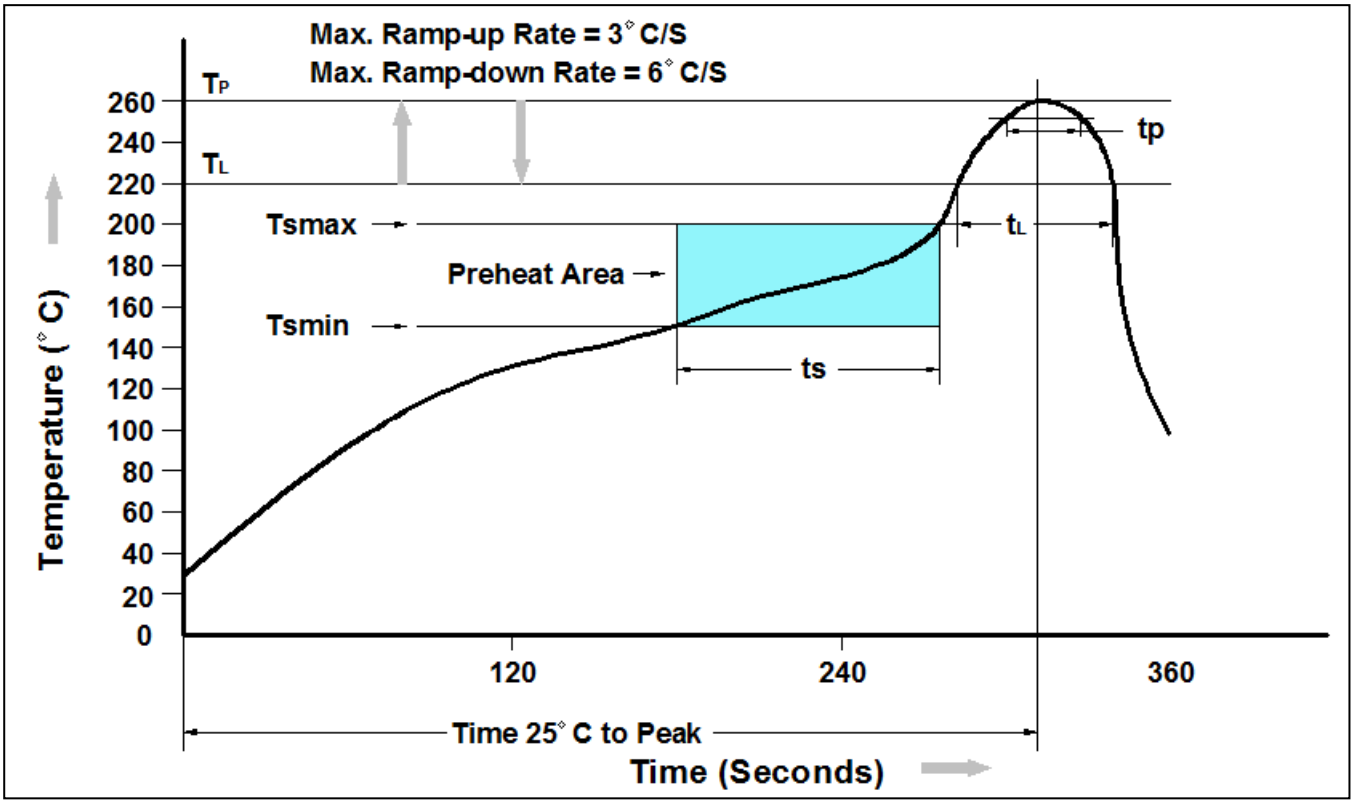


Fig.11 Gate Charge Waveform

➢ Recommand IR Reflow Soldering Thermal Profile

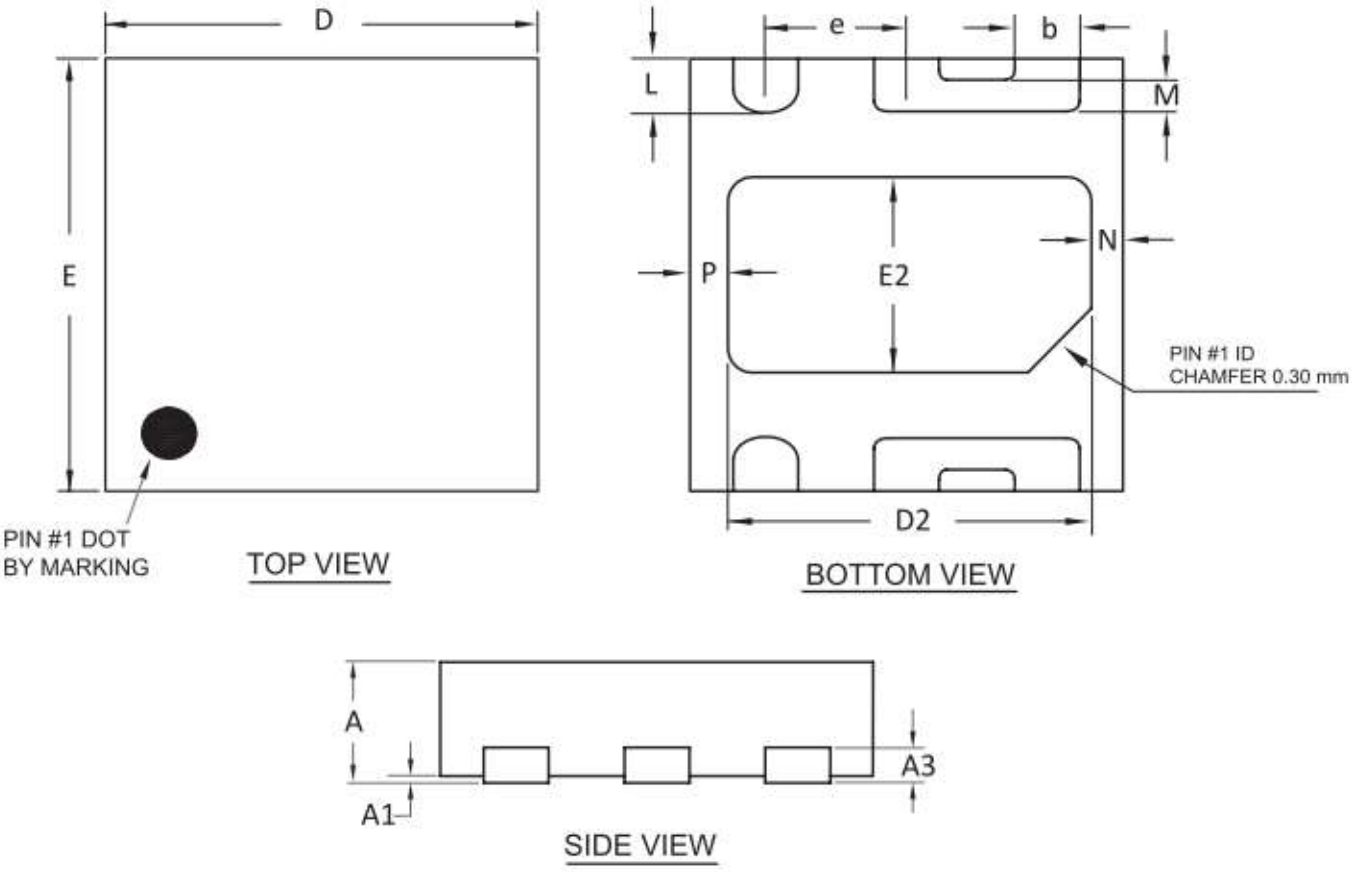


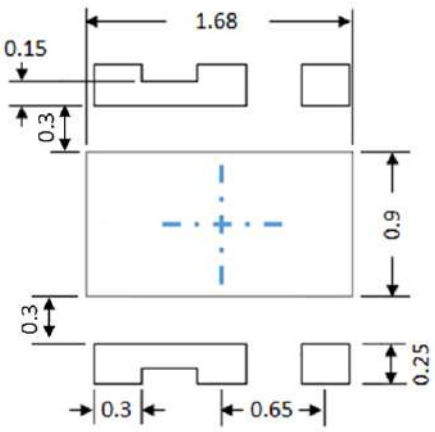
Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Average Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➢ Ordering Information

Part Number	Description	Quantity
PAN82TE36S	DFN2X2A-EP3 Reel	3000 pcs

➢ Package Information (DFN2X2A-EP3)





Recommended Land Pattern

SYMBOLS	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	—	0.550	0.600	—	0.022	0.024
A1	0.000	—	0.050	0.000	—	0.002
A3	0.150 BSC			0.006 BSC		
D	1.950	2.000	2.050	0.077	0.079	0.081
E	1.950	2.000	2.050	0.077	0.079	0.081
D2	1.625	1.675	1.725	0.064	0.066	0.068
E2	0.850	0.900	0.950	0.033	0.035	0.037
L	0.250 BSC			0.010 BSC		
b	0.250	0.300	0.350	0.010	0.012	0.014
e	0.650 BSC			0.026 BSC		
M	0.150 BSC			0.006 BSC		
N	0.150 BSC			0.006 BSC		
P	0.175 BSC			0.007 BSC		

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